## / Descriptions

TO-277

TO-277 Plastic package Ultrafast Recovery Diode.

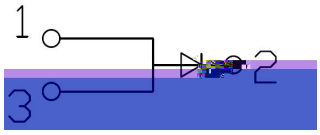
## / Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability. HF Product.

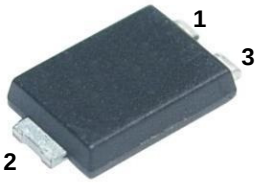
## / Applications

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

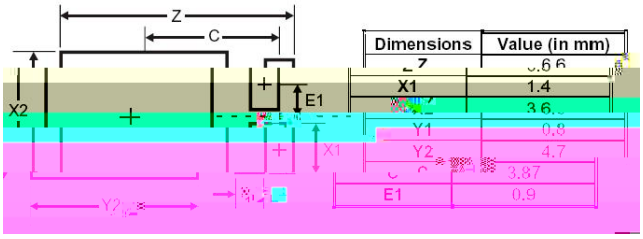
## / Equivalent Circuit




## / Pinning




PIN1 Anode PIN 2 Cathode PIN 3 Anode




Suggested Pad layout

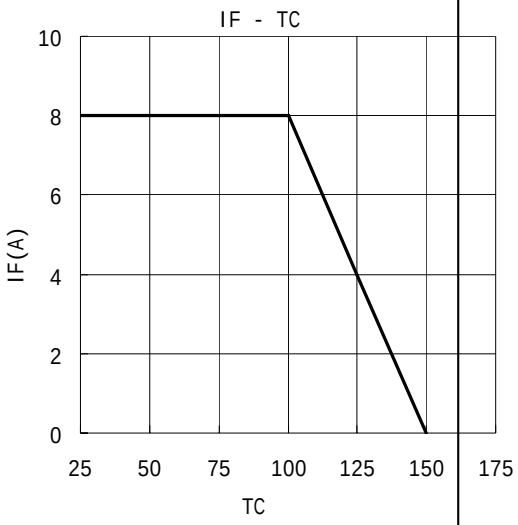
## / $h_{FE}$ Classifications & Marking

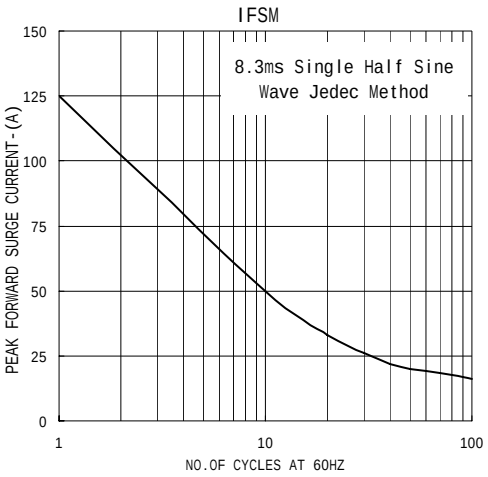
See Marking Instructions.

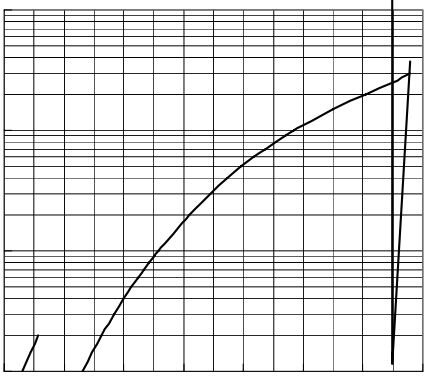
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Peak Repetitive Reverse Voltage | $V_{RRM}$ | 600 | V |
| RMS Reverse voltage | $V_{RMS}$ | 420 | V |
| Average Rectified Forward Current | $I_F$ | 8 | A |
| Non-Repetitive Peak Forward Surge Current | $I_{FSM}$ | 125 | A |
| Thermal Resistance Junction to Case | $R_{Jc}$ | 3.5 | /W |
| Junction and Storage Temperature Range | $T_j$ $T_{stg}$ | -55 150 | |

| Parameter | Symbol | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| Reverse Voltage | $V_{BR}$ | $I_R$=100uA | | 600 | | | V |
| Forward voltage | $V_F$ | $I_F$=8A | Tc=25 | | 1.4 | 1.7 | V |
| | | $I_F$=16A | Tc=25 | | 1.7 | 2.1 | V |
| | | $I_F$=8A | Tc=125 | | 1.4 | 1.7 | V |
| Instantaneous Reverse Current | $I_R$ Note 1 | $V_R$=600V | Ta=25 | | | 5 | uA |
| | | $V_R$=480V | Ta=125 | | | 300 | uA |
| | | $V_R$=600V | Ta=125 | | | 500 | uA |

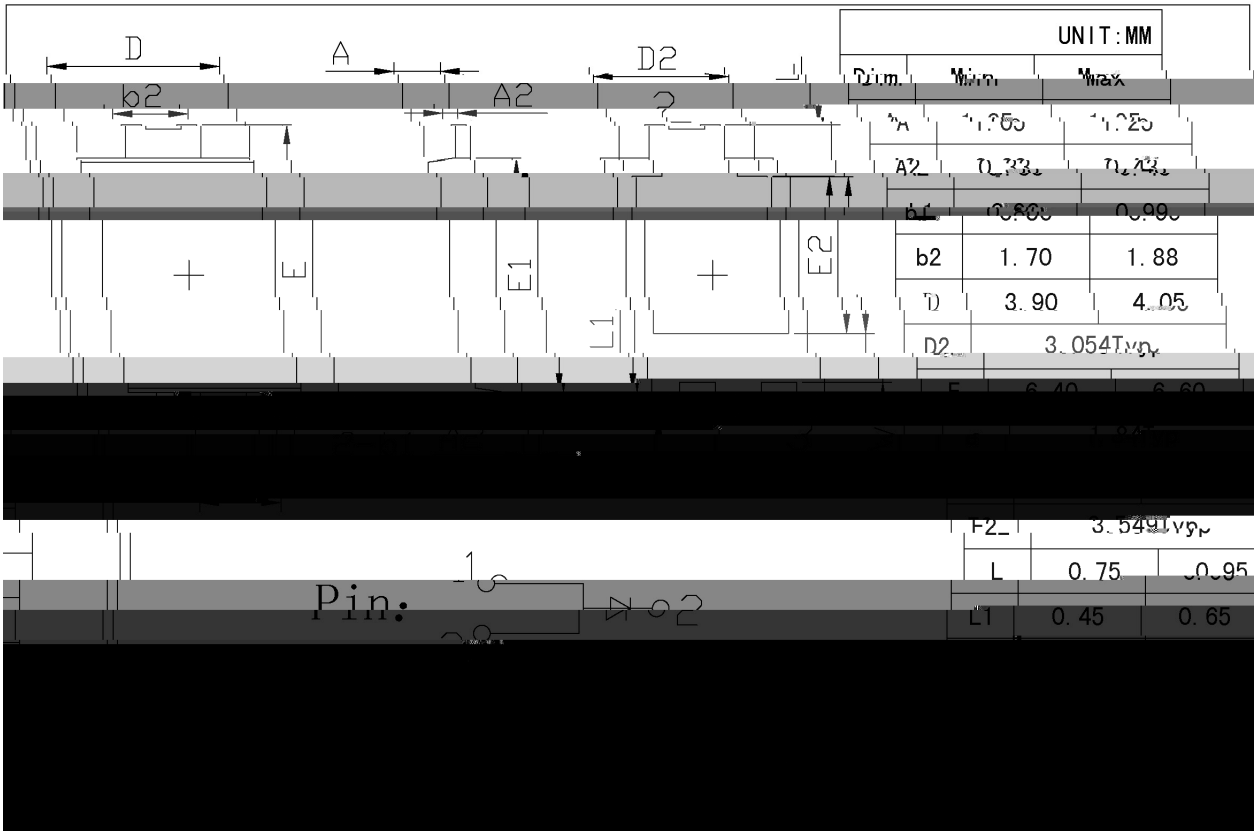
## / Electrical Characteristic Curve



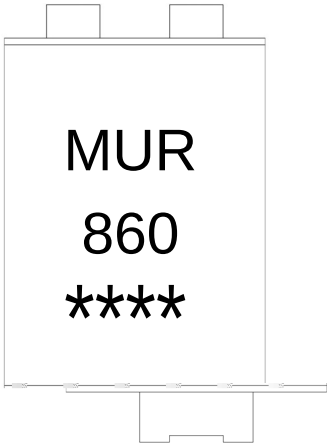



## / Package Dimensions



## / Marking Instructions




MUR860
****

Note:

| | |
|---|---|
| MUR860 | Product Type. |
| ****: | Lot No. Code, code change with Lot No. |